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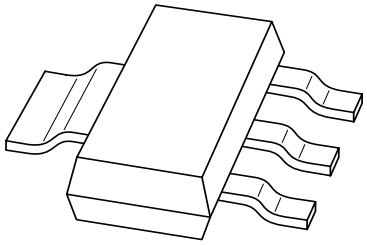
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Kind regards,

Team Nexperia

DATA SHEET



BZV90 series
Voltage regulator diodes

Product data sheet
Supersedes data of 1996 Oct 25

1999 May 17

NXP founded by Philips

Voltage regulator diodes BZV90 series

FEATURES

- Total power dissipation: max. 1500 mW
- Tolerance series: approx. ±5%
- Working voltage range: nom. 2.4 to 75 V (E24 range)
- Non-repetitive peak reverse power dissipation: max. 40 W.

APPLICATIONS

- General regulation functions.

DESCRIPTION

Medium-power voltage regulator diodes in SOT223 plastic SMD packages.

The diodes are available in the normalized E24 approx. ±5% tolerance range. The series consists of 37 types with nominal working voltages from 2.4 to 75 V (BZV90-C2V4 to C75).

PINNING

PIN	DESCRIPTION
1	anode
2, 4	cathode
3	anode

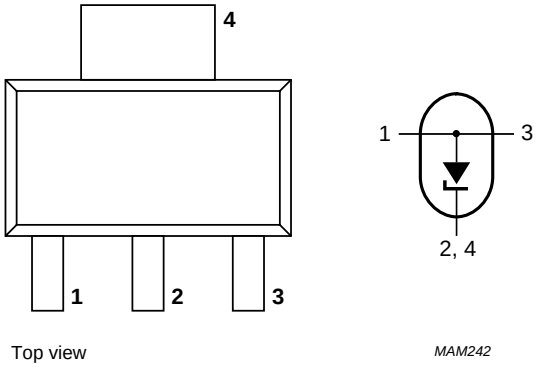


Fig.1 Simplified outline (SOT223) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_F	continuous forward current		–	400	mA
I_{ZSM}	non-repetitive peak reverse current	t_p = 100 μs; square wave; T_j = 25 °C prior to surge	see Table “Per type”		
P_{tot}	total power dissipation	T_{amb} = 25 °C; note 1	–	1500	mW
P_{ZSM}	non-repetitive peak reverse power dissipation	t_p = 100 μs; square wave; T_j = 25 °C prior to surge; see Fig.2	–	40	W
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C

Note

1. Device mounted on an FR4 double-sided copper-clad printed circuit-board; copper area = 2 cm^2.

ELECTRICAL CHARACTERISTICS

Total series

T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_F	forward voltage	I_F = 50 mA; see Fig.3	–	1.0	V

Per type

T_j = 25 °C unless otherwise specified.

BZV90-CXXX	WORKING VOLTAGE V_Z (V) at I_{Ztest}		DIFFERENTIAL RESISTANCE r_{dif} (Ω) at I_{Ztest}		TEMP. COEFF. S_Z (mV/K) at I_{Ztest} see Figs 4 and 5			TEST CURRENT I_{Ztest} (mA)	DIODE CAP. C_d (pF) at f = 1 MHz; at V_R = 0 V	REVERSE CURRENT at REVERSE VOLTAGE		NON-REPETITIVE PEAK REVERSE CURRENT I_{ZSM} (A) at t_p = 100 μs; T_{amb} = 25 °C
										I_R (μA)	V_R (V)	
	MIN.	MAX.	TYP.	MAX.	MIN.	TYP.	MAX.		MAX.	MAX.		MAX.
2V4	2.2	2.6	70	100	–3.5	–1.6	0	5	450	50	1.0	6.0
2V7	2.5	2.9	75	100	–3.5	–2.0	0	5	450	20	1.0	6.0
3V0	2.8	3.2	80	95	–3.5	–2.1	0	5	450	10	1.0	6.0
3V3	3.1	3.5	85	95	–3.5	–2.4	0	5	450	5	1.0	6.0
3V6	3.4	3.8	85	90	–3.5	–2.4	0	5	450	5	1.0	6.0
3V9	3.7	4.1	85	90	–3.5	–2.5	0	5	450	3	1.0	6.0
4V3	4.0	4.6	80	90	–3.5	–2.5	0	5	450	3	1.0	6.0
4V7	4.4	5.0	50	80	–3.5	–1.4	0.2	5	300	3	2.0	6.0
5V1	4.8	5.4	40	60	–2.7	–0.8	1.2	5	300	2	2.0	6.0
5V6	5.2	6.0	15	40	–2.0	1.2	2.5	5	300	1	2.0	6.0
6V2	5.8	6.6	6	10	0.4	2.3	3.7	5	200	3	4.0	6.0
6V8	6.4	7.2	6	15	1.2	3.0	4.5	5	200	2	4.0	6.0
7V5	7.0	7.9	6	15	2.5	4.0	5.3	5	150	1	5.0	4.0
8V2	7.7	8.7	6	15	3.2	4.6	6.2	5	150	0.7	5.0	4.0
9V1	8.5	9.6	6	15	3.8	5.5	7.0	5	150	0.5	6.0	3.0
10	9.4	10.6	8	20	4.5	6.4	8.0	5	90	0.2	7.0	3.0
11	10.4	11.6	10	20	5.4	7.4	9.0	5	85	0.1	8.0	2.5
12	11.4	12.7	10	25	6.0	8.4	10.0	5	85	0.1	8.0	2.5
13	12.4	14.1	10	30	7.0	9.4	11.0	5	80	0.1	8.0	2.5
15	13.8	15.6	10	30	9.2	11.4	13.0	5	75	0.05	10.5	2.0
16	15.3	17.1	10	40	10.4	12.4	14.0	5	75	0.05	11.2	1.5
18	16.8	19.1	10	45	12.4	14.4	16.0	5	70	0.05	12.6	1.5
20	18.8	21.2	15	55	14.4	16.4	18.0	5	60	0.05	14.0	1.5

BZV90-CXXX	WORKING VOLTAGE V_Z (V) at I_{Ztest}		DIFFERENTIAL RESISTANCE r_{dif} (Ω) at I_{Ztest}		TEMP. COEFF. S_Z (mV/K) at I_{Ztest} see Figs 4 and 5			TEST CURRENT I_{Ztest} (mA)	DIODE CAP. C_d (pF) at f = 1 MHz; at V_R = 0 V	REVERSE CURRENT at REVERSE VOLTAGE		NON-REPETITIVE PEAK REVERSE CURRENT I_{ZSM} (A) at t_p = 100 μs; T_{amb} = 25 °C
	MIN.	MAX.	TYP.	MAX.	MIN.	TYP.	MAX.		MAX.	I_R (μA) MAX.	V_R (V)	MAX.
22	20.8	23.3	20	55	16.4	18.4	20.0	5	60	0.05	15.4	1.25
24	22.8	25.6	25	70	18.4	20.4	22.0	5	55	0.05	16.8	1.25
27	25.0	28.9	25	80	21.4	23.4	25.3	2	50	0.05	18.9	1.0
30	28.0	32.0	30	80	24.4	26.6	29.4	2	50	0.05	21.0	1.0
33	31.0	35.0	35	80	27.4	29.7	33.4	2	45	0.05	23.1	0.9
36	34.0	38.0	35	90	30.4	33.0	37.4	2	45	0.05	25.2	0.8
39	37.0	41.0	40	130	33.4	36.4	41.2	2	45	0.05	27.3	0.7
43	40.0	46.0	45	150	37.6	41.2	46.6	2	40	0.05	30.1	0.6
47	44.0	50.0	50	170	42.0	46.1	51.8	2	40	0.05	32.9	0.5
51	48.0	54.0	60	180	46.6	51.0	57.2	2	40	0.05	35.7	0.4
56	52.0	60.0	70	200	52.2	57.0	63.8	2	40	0.05	39.2	0.3
62	58.0	66.0	80	215	58.8	64.4	71.6	2	35	0.05	43.4	0.3
68	64.0	72.0	90	240	65.6	71.7	79.8	2	35	0.05	47.6	0.25
75	70.0	79.0	95	255	73.4	80.2	88.6	2	35	0.05	52.5	0.2

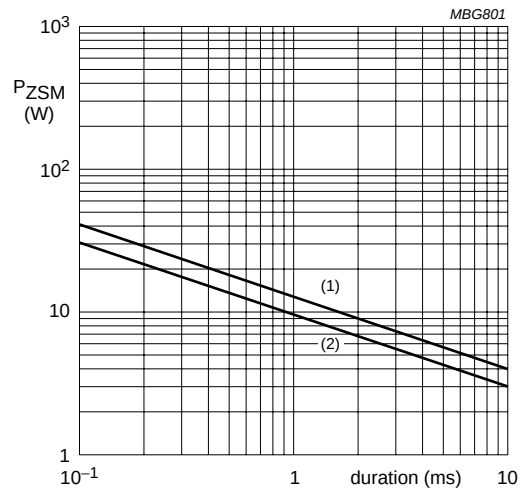
THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	lead length max.; note 1	83.3	K/W

Note

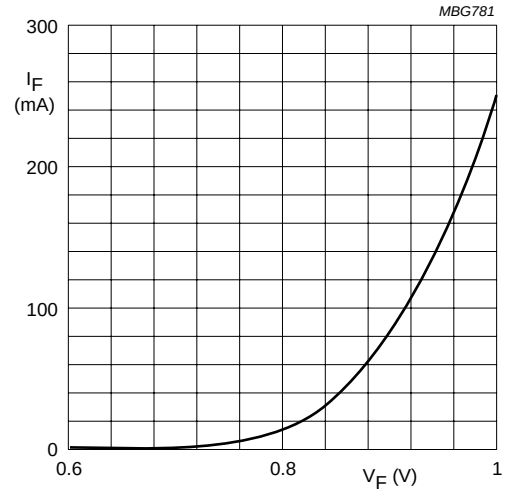
1. Device mounted on an FR4 double-sided copper-clad printed circuit-board; copper area = 2 cm^2.

GRAPHICAL DATA



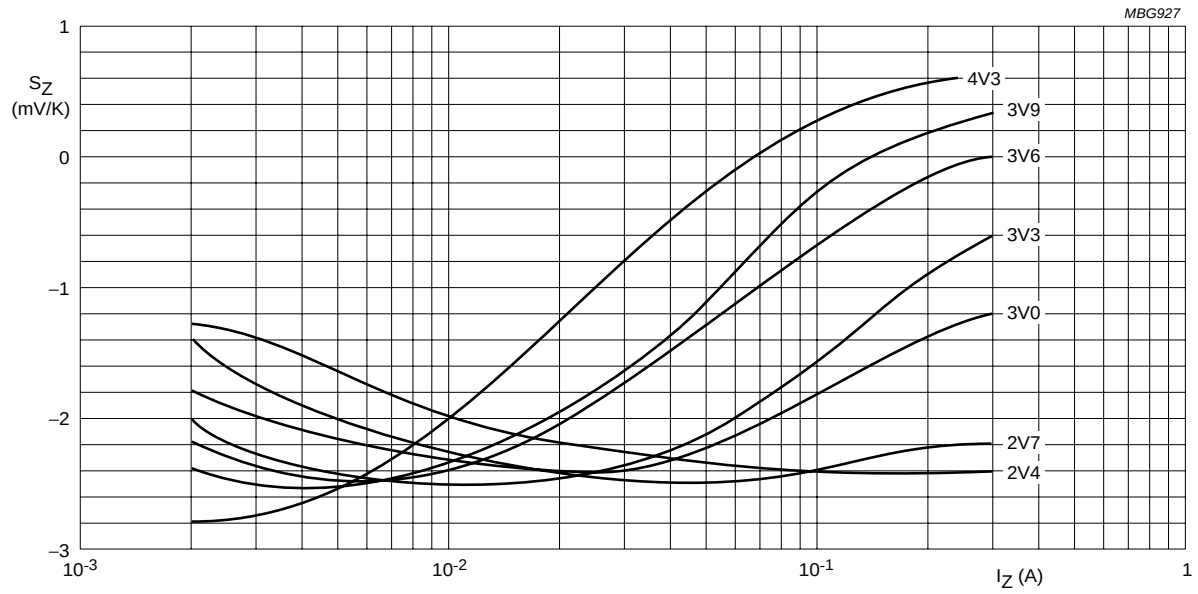
(1) T_j = 25 °C (prior to surge).
(2) T_j = 150 °C (prior to surge).

Fig.2 Maximum permissible non-repetitive peak reverse power dissipation versus duration.



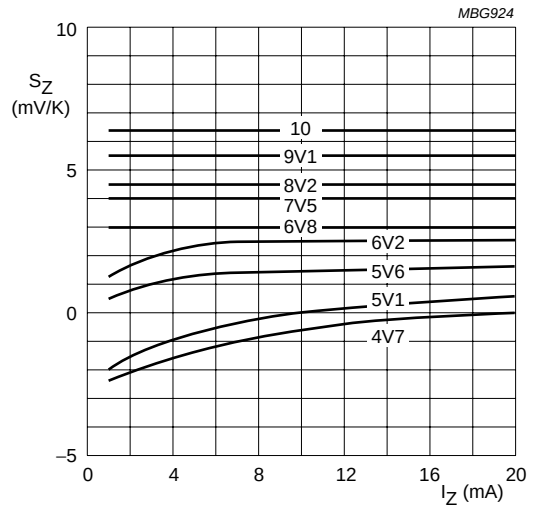
T_j = 25 °C.

Fig.3 Forward current as a function of forward voltage; typical values.



BZV90-C2V4 to C4V3.
T_j = 25 to 150 °C.

Fig.4 Temperature coefficient as a function of working current; typical values.

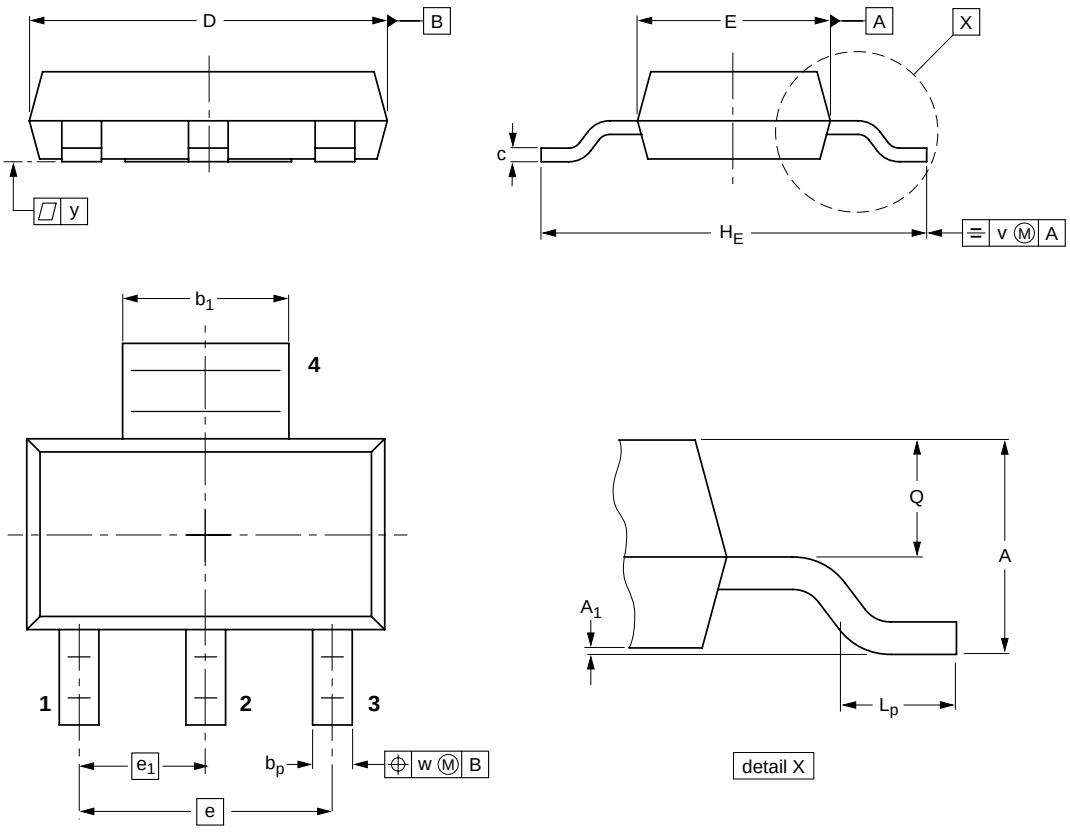


BZV90-C4V7 to C10.
T_j = 25 to 150 °C.

Fig.5 Temperature coefficient as a function of working current; typical values.

PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 4 leads **SOT223**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b_p	b_1	c	D	E	e	e_1	H_E	L_p	Q	v	w	y
mm	1.8 1.5	0.10 0.01	0.80 0.60	3.1 2.9	0.32 0.22	6.7 6.3	3.7 3.3	4.6	2.3	7.3 6.7	1.1 0.7	0.95 0.85	0.2	0.1	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT223			SC-73			~~97-02-28~~ 99-09-13

DATA SHEET STATUS

DOCUMENT STATUS[1]	PRODUCT STATUS[2]	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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NXP Semiconductors

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This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

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